

New Jersey Semi-Conductor Products, Inc.

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2N4863
2N4864

SILICON NPN TRANSISTORS

These double diffused, epitaxial collector devices are oxide passivated. They are designed for use in switching and many amplifier applications. The latest technologies are used to provide optimum performance and the highest degree of reliability.

NPN
120V
2.0 AMP SWITCHING

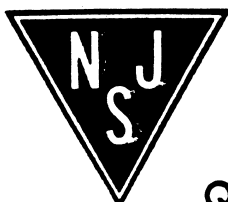
TO-5 & TO-66*

*2N4863, Case TO-5; 2N4864, Case TO-66.

MAXIMUM RATINGS (T _a = 25°C unless otherwise noted)					
SYMBOL	PARAMETER	2N4863	2N4864	UNIT	
V _{CE}	Collector-Emitter Voltage	140	140	Volts	
V _{CE(sat)}	Collector-Emitter Voltage (sat.)	120	120	Volts	
V _{BE}	Base-Emitter Voltage	8.0	8.0	Volts	
I _C	Collector Current (Continuous)	2.0	2.0	Amps	
I _B	Base Current (Continuous)	0.5	0.5	Amps	
P _T	Total Power Dissipation (T _a = 25°C)	4.0	16	Watts	
θ _{JA}	Junction-to-Air Thermal Resistance	25	6.25	°C/W	
T _J	Junction Temperature	-55 to +200	-55 to +200	°C	

ELECTRICAL CHARACTERISTICS (T _a = 25°C unless otherwise noted)					
SYMBOL	PARAMETER	2N4863	2N4864	UNIT	
V _{CE}	Collector-Emitter Voltage	120	120	Volts	
I _B	Base Current	10	10	μA	
I _C	Collector Current	10	10	μA	
I _B	Base Current	0.1	0.1	μA	
I _C	Collector Current	10	10	μA	
I _B	Base Current	10	10	μA	
I _C	Collector Current	10	10	μA	
V _{CE}	Collector-Emitter Voltage	15	15	Volts	
I _B	Base Current	150	150	μA	
V _{CE}	Collector-Emitter Voltage	1.5	1.5	Volts	
I _B	Base Current	0.2	0.2	μA	
V _{CE}	Collector-Emitter Voltage	1.5	1.5	Volts	
I _B	Base Current	5.0	5.0	μA	
C _{IE}	Emitter-Base Capacitance	50	50	pF	

† Pulse Measurement Conditions: Length = 300μs, Duty Cycle ≤ 2% (measured using separate current carrying and voltage sensing leads).



Quality Semi-Conductors